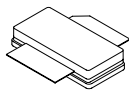


AGR19060E

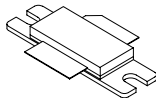
60 W, 1930 MHz—1990 MHz, PCS LDMOS RF Power Transistor

Introduction

The AGR19060E is a 60 W, 28 V N-channel laterally diffused metal oxide semiconductor (LDMOS) RF power field effect transistor (FET) suitable for personal communication service (PCS) (1930 MHz—1990 MHz), global system for mobile communication (GSM/EDGE), time-division multiple access (TDMA), and single-carrier or multicarrier class AB power amplifier applications.



AGR19060EU (unflanged)



AGR19060EF (flanged)

Figure 1. Available Packages

N-CDMA Features

- Typical 2 carrier N-CDMA performance: $V_{DD} = 28$ V, $I_{DQ} = 700$ mA, $f_1 = 1958.75$ MHz, $f_2 = 1961.25$ MHz, IS-95 CDMA (pilot, sync, paging, traffic codes 8—13). Peak/average (P/A) = 9.72 dB at 0.01% probability on CCDF. 1.2288 MHz transmission bandwidth (BW). Adjacent channel power ratio (ACPR) measured over 30 kHz BW at $f_1 - 885$ kHz and $f_2 + 885$ kHz. Third-order intermodulation distortion (IM3) measured over a 1.2288 MHz BW at $f_1 - 2.5$ MHz and $f_2 + 2.5$ MHz.
- Output power (P_{OUT}): 12 W.
 - Power gain: 15.5 dB.
 - Efficiency: 23.5%.
 - IM3: -36 dBc.
 - ACPR: -50.5 dBc.

EDGE Features

- Typical EDGE performance (1960 MHz, 26 V, $I_{DQ} = 500$ mA):
- Output power (P_{OUT}): 25 W.
 - Power gain: 15.3 dB.
 - Efficiency: 37%.
 - Modulation spectrum:
 - @ ± 400 kHz = -61.0 dBc.
 - @ ± 600 kHz = -74.0 dBc.
 - Error vector magnitude (EVM) = 2.5%.

GSM Features

- Typical performance over entire GSM band:
- P1dB: 60 W typical.
 - Continuous wave (CW) power gain: @ P1dB = 14.5 dB.
 - CW efficiency @ P1dB = 53% typical.
 - Return loss: -12 dB.

Device Performance Features

- High-reliability, gold-metalization process.
- Low hot carrier injection (HCI) induced bias drift over 20 years.
- Internally matched.
- High gain, efficiency, and linearity.
- Integrated ESD protection.
- Device can withstand 10:1 voltage standing wave ratio (VSWR) at 28 Vdc, 1930 MHz, 60 W CW output power.
- Large signal impedance parameters available.

ESD Rating*

AGR19060E	Minimum (V)	Class
HBM	500	1B
MM	50	A
CDM	1500	4

* Although electrostatic discharge (ESD) protection circuitry has been designed into this device, proper precautions must be taken to avoid exposure to ESD and electrical overstress (EOS) during all handling, assembly, and test operations. PEAK Devices employs a human-body model (HBM), a machine model (MM), and a charged-device model (CDM) qualification requirement in order to determine ESD-susceptibility limits and protection design evaluation. ESD voltage thresholds are dependent on the circuit parameters used in each of the models, as defined by JEDEC's JESD22-A114B (HBM), JESD22-A115A (MM), and JESD22-C101A (CDM) standards.

Caution: MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

Electrical Characteristics

Table 1. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Case: AGR19060EU	$R_{\theta JC}$	1.00	$^{\circ}\text{C}/\text{W}$
AGR19060EF	$R_{\theta JC}$	1.00	$^{\circ}\text{C}/\text{W}$

Table 2. Absolute Maximum Ratings*

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DSS}	65	Vdc
Gate-source Voltage	V_{GS}	-0.5, 15	Vdc
Total Dissipation at $T_c = 25^{\circ}\text{C}$: AGR19060EU	P_D	175	W
AGR19060EF	P_D	175	W
Derate Above 25°C : AGR19060EU	—	1.00	$\text{W}/^{\circ}\text{C}$
AGR19060EF	—	1.00	$\text{W}/^{\circ}\text{C}$
Operating Junction Temperature	T_J	200	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65, 150	$^{\circ}\text{C}$

* Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Recommended operating conditions apply unless otherwise specified: $T_c = 30^{\circ}\text{C}$.

Table 3. dc Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-source Breakdown Voltage ($V_{GS} = 0\text{ V}$, $I_D = 300\mu\text{A}$)	$V_{(BR)DSS}$	65	—	—	Vdc
Gate-source Leakage Current ($V_{GS} = 5\text{ V}$, $V_{DS} = 0\text{ V}$)	I_{GSS}	—	—	1.8	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ V}$, $V_{GS} = 0\text{ V}$)	I_{DSS}	—	—	100	μAdc
On Characteristics					
Forward Transconductance ($V_{DS} = 10\text{ V}$, $I_D = 0.45\text{ A}$)	G_{FS}	—	4.0	—	S
Gate Threshold Voltage ($V_{DS} = 10\text{ V}$, $I_D = 180\mu\text{A}$)	$V_{GS(th)}$	—	—	4.8	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ V}$, $I_D = 500\text{ mA}$)	$V_{GS(Q)}$	—	3.6	—	Vdc
Drain-source On-voltage ($V_{GS} = 10\text{ V}$, $I_D = 0.45\text{ A}$)	$V_{DS(on)}$	—	0.08	—	Vdc

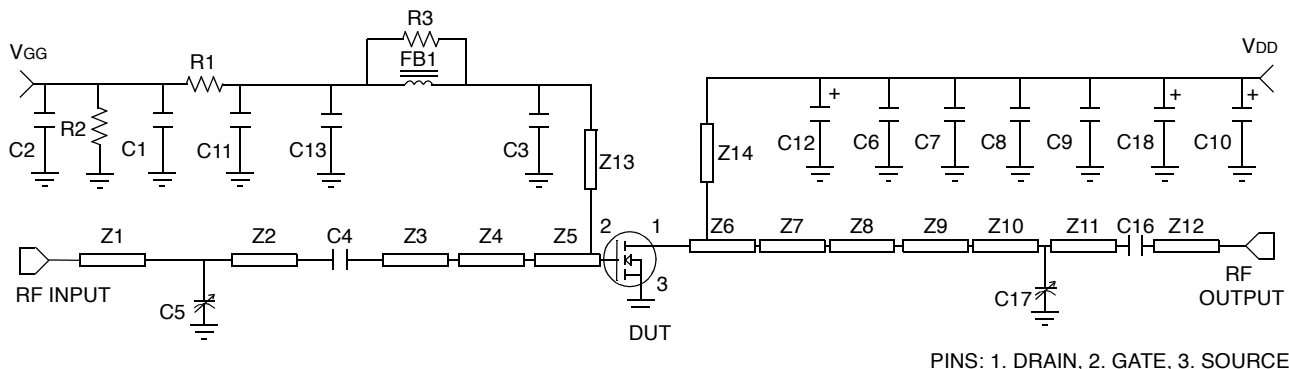
Electrical Characteristics (continued)

Recommended operating conditions apply unless otherwise specified: $T_c = 30\text{ }^\circ\text{C}$.

Table 4. RF Characteristics

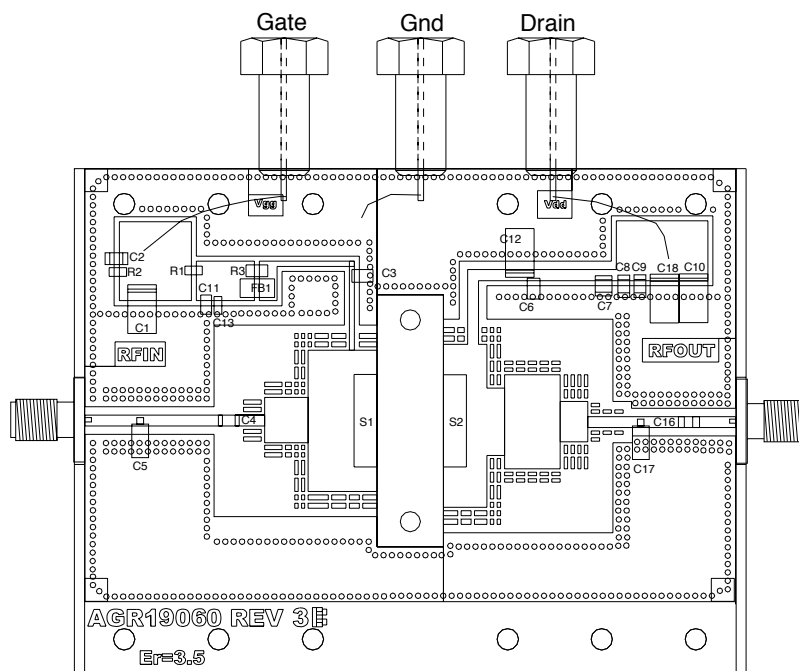
Parameter	Symbol	Min	Typ	Max	Unit
Dynamic Characteristics					
Transfer Capacitance ($V_{DS} = 28\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$) (Part is internally matched both on input and output.)	CRSS	—	1.3	—	pF
Functional Tests (in Supplied Test Fixture)					
Common-source Amplifier Power Gain ($V_{DD} = 28\text{ Vdc}$, $P_{OUT} = 12\text{ W}$ average, 2-Carrier N-CDMA, $I_{DQ} = 700\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1932.5\text{ MHz}$ and $f_1 = 1987.5\text{ MHz}$, $f_2 = 1990\text{ MHz}$)	GPS	14.5	15.5	—	dB
Drain Efficiency ($V_{DD} = 28\text{ Vdc}$, $P_{OUT} = 12\text{ W}$ average, 2-Carrier N-CDMA, $I_{DQ} = 700\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1932.5\text{ MHz}$ and $f_1 = 1987.5\text{ MHz}$, $f_2 = 1990\text{ MHz}$)	η	—	23.5	—	%
Third-order Intermodulation Distortion ($V_{DD} = 28\text{ Vdc}$, $P_{OUT} = 12\text{ W}$ average, 2-Carrier N-CDMA, $I_{DQ} = 700\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1932.5\text{ MHz}$ and $f_1 = 1987.5\text{ MHz}$, $f_2 = 1990\text{ MHz}$; IM3 measured in a 1.2288 MHz integration BW centered at $f_1 - 2.5\text{ MHz}$ and $f_2 + 2.5\text{ MHz}$, referenced to the carrier channel power)	IM3	—	-36	—	dBc
Adjacent Channel Power Ratio ($V_{DD} = 28\text{ Vdc}$, $P_{OUT} = 12\text{ W}$ average, 2-Carrier N-CDMA, $I_{DQ} = 700\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1932.5\text{ MHz}$ and $f_1 = 1987.5\text{ MHz}$, $f_2 = 1990\text{ MHz}$; ACPR measured in a 1.2288 MHz integration BW centered at $f_1 - 2.5\text{ MHz}$ and $f_2 + 2.5\text{ MHz}$, referenced to the carrier channel power)	ACPR	—	-50.5	—	dBc
Input Return Loss ($V_{DD} = 28\text{ Vdc}$, $P_{OUT} = 12\text{ W}$ average, 2-Carrier N-CDMA, $I_{DQ} = 700\text{ mA}$, $f_1 = 1930\text{ MHz}$, $f_2 = 1932.5\text{ MHz}$ and $f_1 = 1987.5\text{ MHz}$, $f_2 = 1990\text{ MHz}$)	IRL	—	-12	—	dB
Output Power at 1 dB Gain Compression ($V_{DD} = 28\text{ V}$, $P_{OUT} = 60\text{ W CW}$, $f = 1990\text{ MHz}$, $I_{DQ} = 500\text{ mA}$)	P1dB	60	70	—	W
Ruggedness ($V_{DD} = 28\text{ V}$, $P_{OUT} = 60\text{ W CW}$, $I_{DQ} = 350\text{ mA}$, $f = 1930\text{ MHz}$, $V_{SWR} = 10:1$ [all phase angles])	Ψ	No degradation in output power.			

Test Circuit Illustrations for AGR19060E



PINS: 1. DRAIN, 2. GATE, 3. SOURCE

A. Schematic



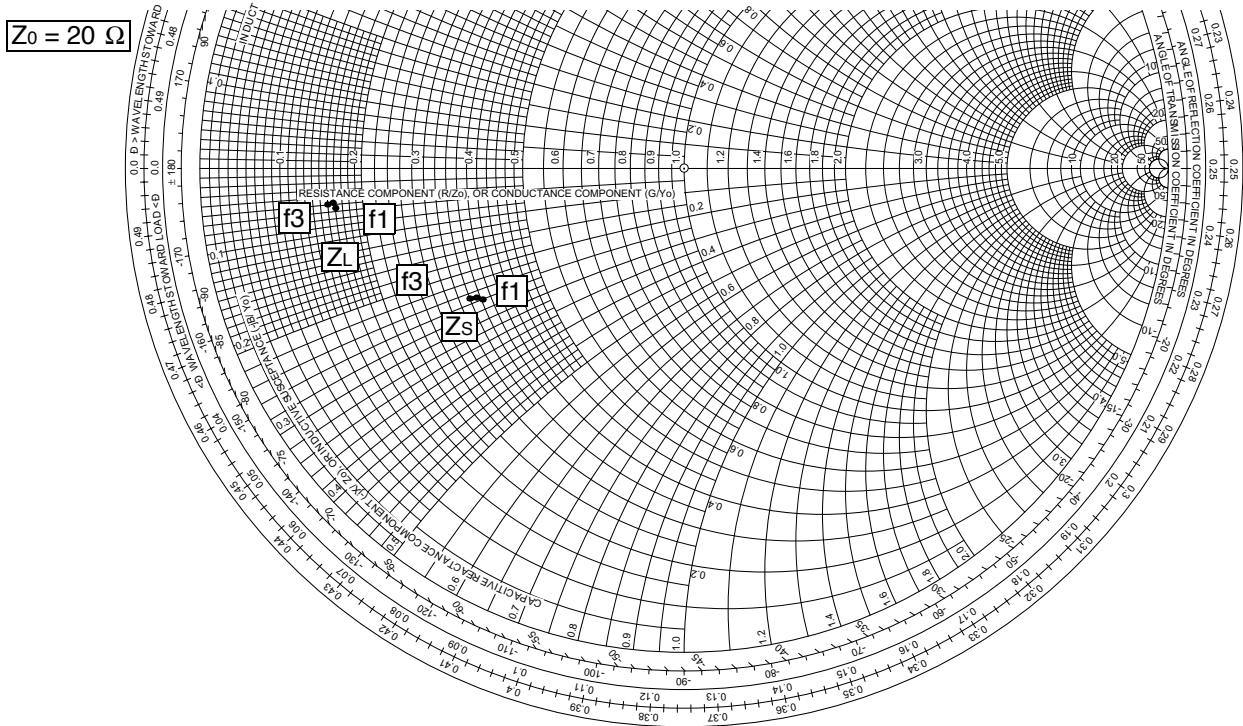
B. Component Layout

Parts List:

- Microstrip line: Z1 0.330 in. x 0.065 in.; Z2 0.470 in. x 0.065 in.; Z3 0.175 in. x 0.065 in.; Z4 0.260 in. x 0.270 in.; Z5 0.410 in. x 0.840 in.; Z6 0.260 in. x 0.970 in.; Z7 0.105 in. x 0.400 in.; Z8 0.330 in. x 0.560 in.; Z9 0.165 in. x 0.240 in.; Z10 0.315 in. x 0.065 in.; Z11 0.260 in. x 0.065 in.; Z12 0.255 in. x 0.065 in.; Z13 0.440 in. x 0.030 in.; Z14 0.695 in. x 0.050 in.
- ATC[®] B case chip capacitors: C3, C6: 8.2 pF, 100B8R2JCA500X; C4, C16: 10 pF, 100B100JCA500X; C7: 1000 pF, 100B102JCA500X.
- Kemet[®] B case chip capacitors: C9, C11: 0.10 μ F, CDR33BX104AKWS.
- Johanson Giga-Trim[®] variable capacitors: C5, C17: 0.4 pF—2.5 pF.
- Vitramon[®] 1206: C2, C8: 22000 pF.
- Murata[®] 0805: C13: 0.01 μ F, GRM40X7R103K100AL.
- Fair-Rite[®] ferrite bead: FB1, #2743019447.
- Sprague[®] tantalum, SMT, 35 V: C1, C10, C12: 22 μ F; C18: 10 μ F.
- Fixed film chip resistors, 0.25 W, 0.08 x 0.13: R1 510 Ω ; R2 560 k Ω ; R3 4.7 Ω .
- PCB etched circuit boards.
- Taconic[®] ORCER RF-35: board material, 1 oz. copper, 30 mil thickness, $\epsilon_r = 3.5$.

Figure 2. AGR19060E Test Circuit Schematic

Typical Performance Characteristics



MHz (f)	$Z_s \Omega$ (Complex Source Impedance)	$Z_L \Omega$ (Complex Optimum Load Impedance)
1930 (f1)	$7.24 - j5.20$	$3.23 - j1.07$
1960 (f2)	$7.04 - j5.00$	$3.06 - j0.99$
1990 (f3)	$6.87 - j4.96$	$2.97 - j1.00$

Note: Z_L was chosen based on trade-offs between gain, output power, drain efficiency, and intermodulation distortion.

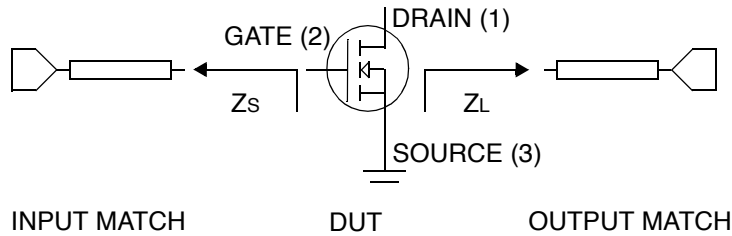
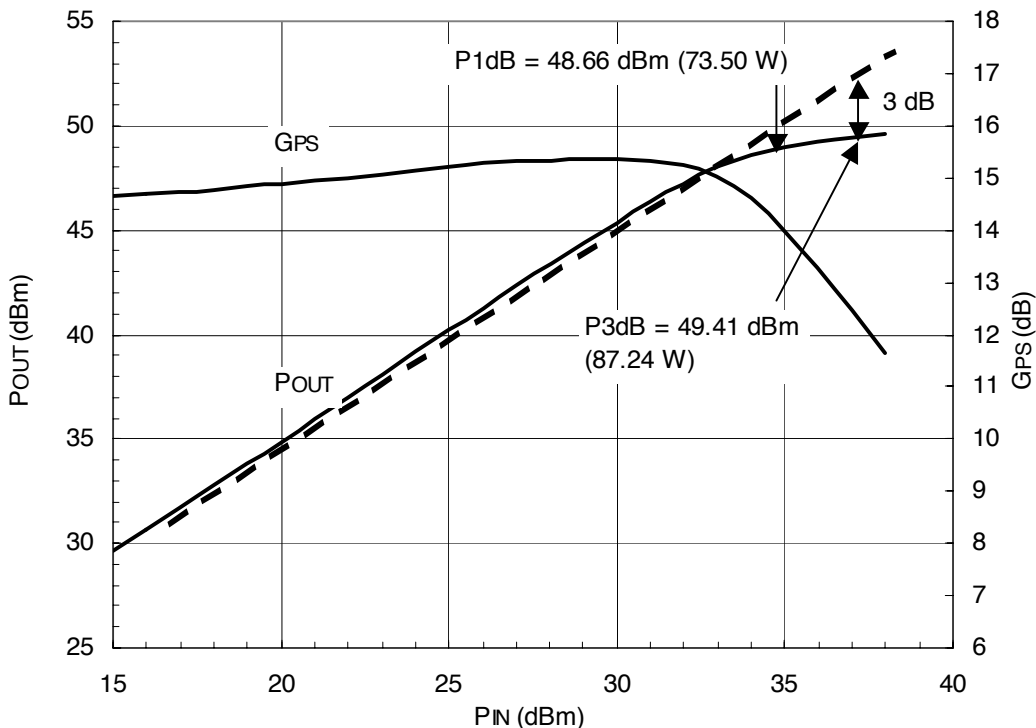


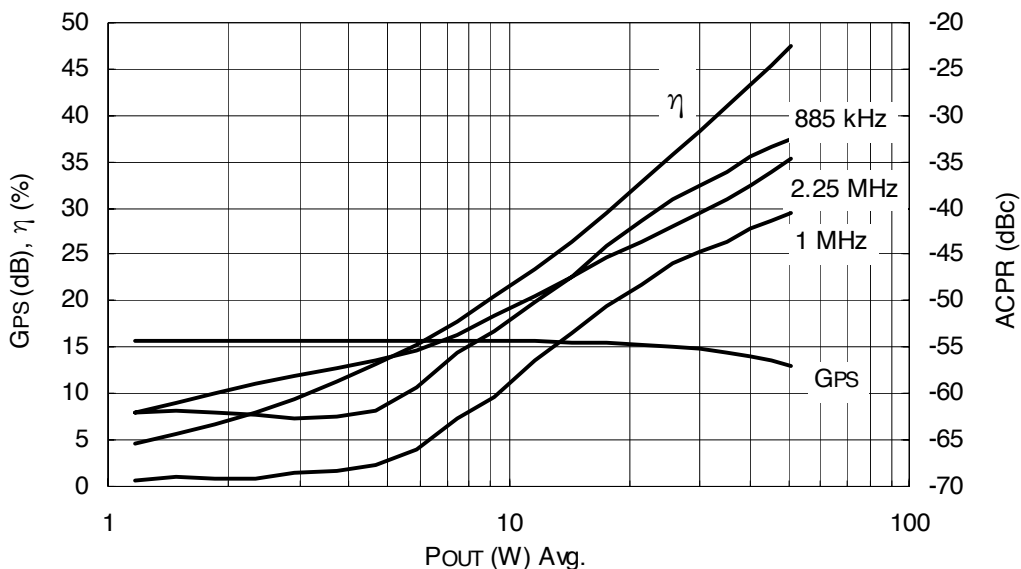
Figure 3. Series Equivalent Input and Output Impedances

Typical Performance Characteristics (continued)



Test Conditions:
 $V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 500 \text{ mA}$, CW, center frequency = 1960 MHz.

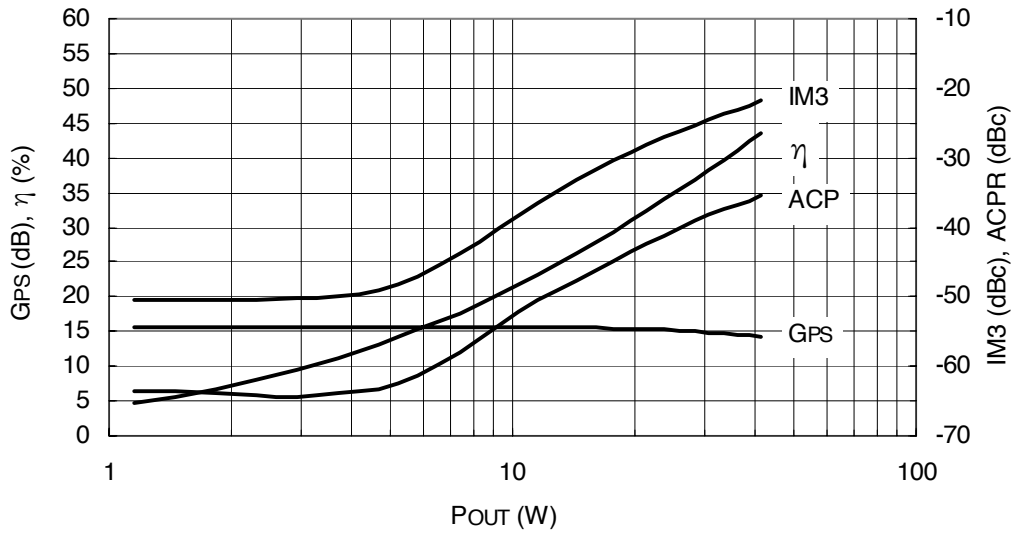
Figure 4. CW POUT vs. PIN



Test Conditions:
 $V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 700 \text{ mA}$, $f = 1960 \text{ MHz}$, N-CDMA, 2.5 MHz @ 1.2288 MHz BW, P/A = 9.72 dB @ 0.01% probability (CCDF), channel spacing (BW) 885 kHz (30 kHz), 1.25 MHz (12.5 kHz), 2.25 MHz (1 MHz).

Figure 5. N-CDMA ACPR, Power Gain, and Drain Efficiency vs. POUT

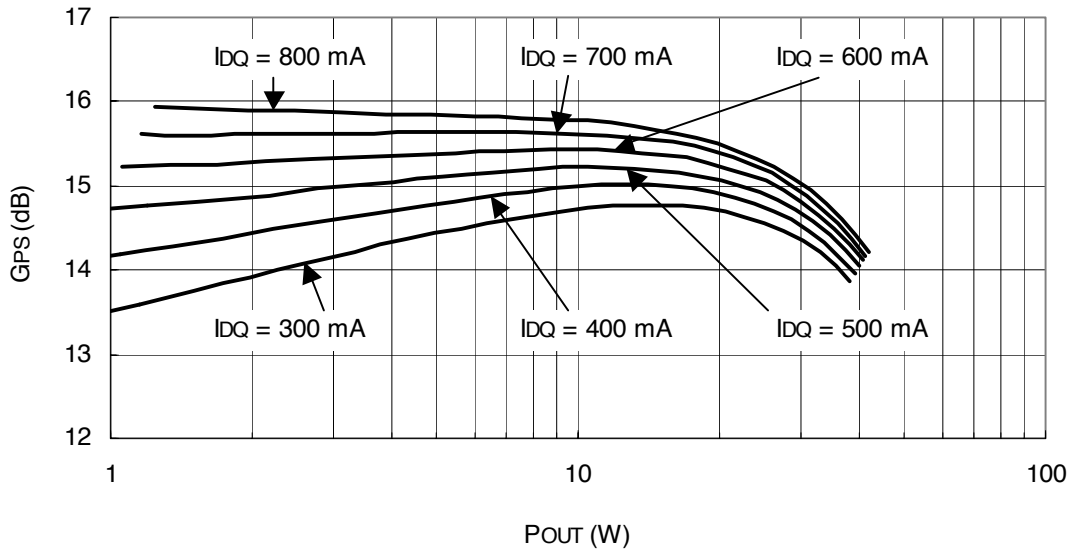
Typical Performance Characteristics (continued)



Test Conditions:

$V_{DD} = 28$ Vdc, $I_{DQ} = 700$ mA, $f_1 = 1958.75$ MHz, $f_2 = 1961.25$ MHz, 2 x N-CDMA, 2.5 MHz @ 1.2288 MHz BW, P/A = 9.72 dB @ 0.01% probability (CCDF), channel spacing (BW) ACPR: 885 kHz (30 kHz), IM3: 2.5 MHz (1.2288 MHz).

Figure 6. 2-Carrier N-CDMA ACPR, IM3, Power Gain, and Drain Efficiency vs. Pout

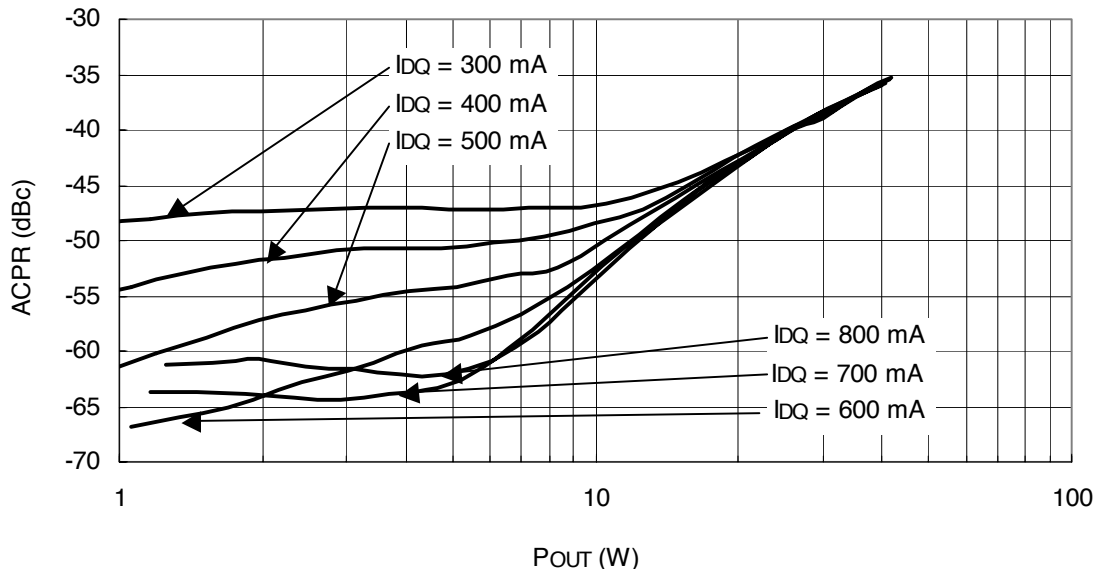


Test Conditions:

$V_{DD} = 28$ Vdc, $f_1 = 1958.75$ MHz, $f_2 = 1961.25$ MHz, 2 carrier N-CDMA measurement.

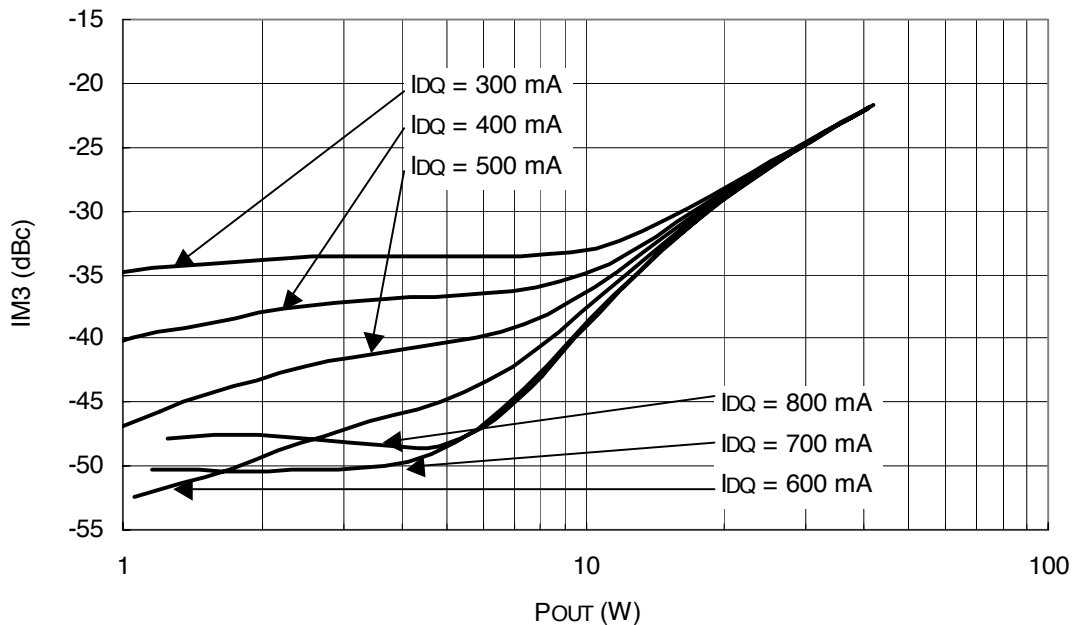
Figure 7. 2-Carrier N-CDMA Power Gain vs. Pout

Typical Performance Characteristics (continued)



Test Conditions:
VDD = 28 Vdc, f1 = 1958.75 MHz, f2 = 1961.25 MHz, 2 carrier N-CDMA measurement.

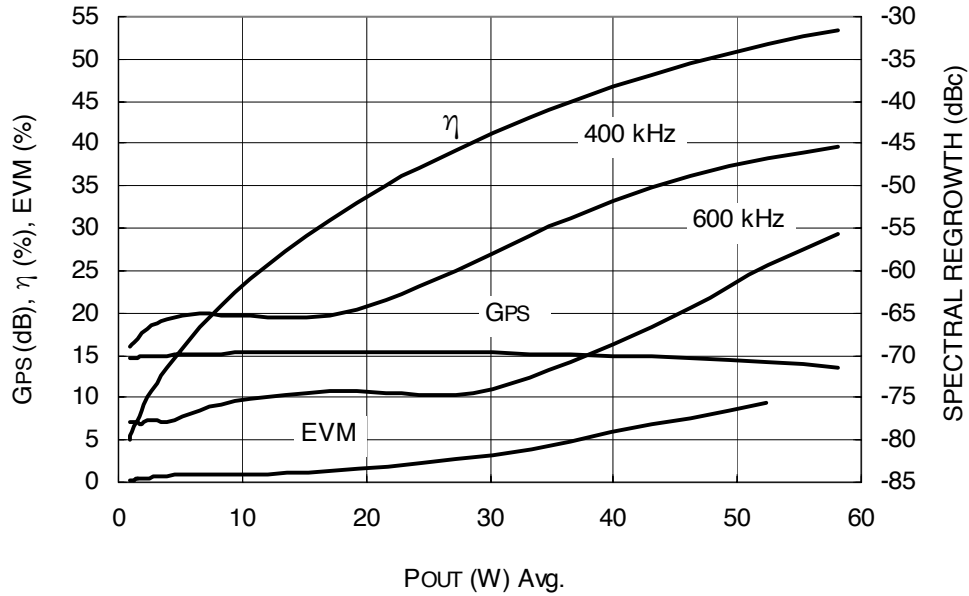
Figure 8. ACPR vs. Pout



Test Conditions:
VDD = 28 Vdc, f1 = 1958.75 MHz, f2 = 1961.25 MHz, 2 carrier N-CDMA measurement.

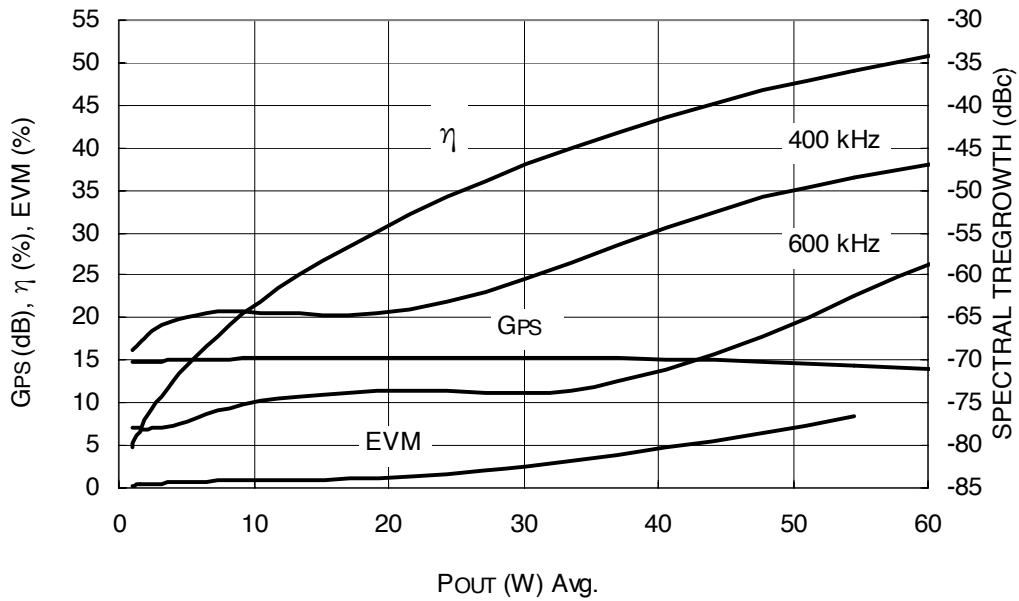
Figure 9. IM3 vs. Pout

Typical Performance Characteristics (continued)



Test Conditions:
 V_{DD} = 26 Vdc, I_{DQ} = 500 mA, f = 1960 MHz, modulation = GSM/EDGE.

Figure 10. GSM/EDGE Power Gain, Drain Efficiency, Spectral Regrowth, and EVM vs. Pout



Test Conditions:
 V_{DD} = 28 Vdc, I_{DQ} = 500 mA, f = 1960 MHz, modulation = GSM/EDGE.

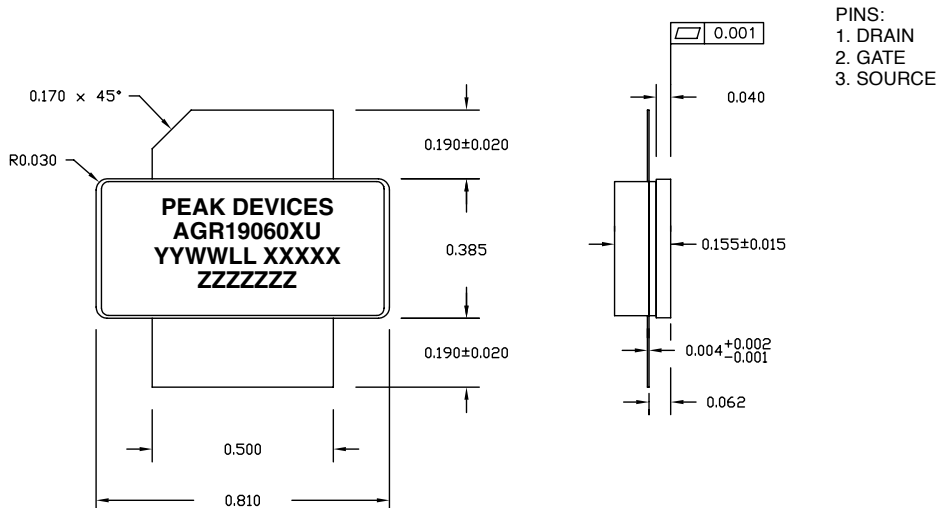
Figure 11. GSM/EDGE Power Gain, Drain Efficiency, Spectral Regrowth, and EVM vs. Pout

AGR19060E
60 W, 1930 MHz—1990 MHz, PCS LDMOS RF Power Transistor

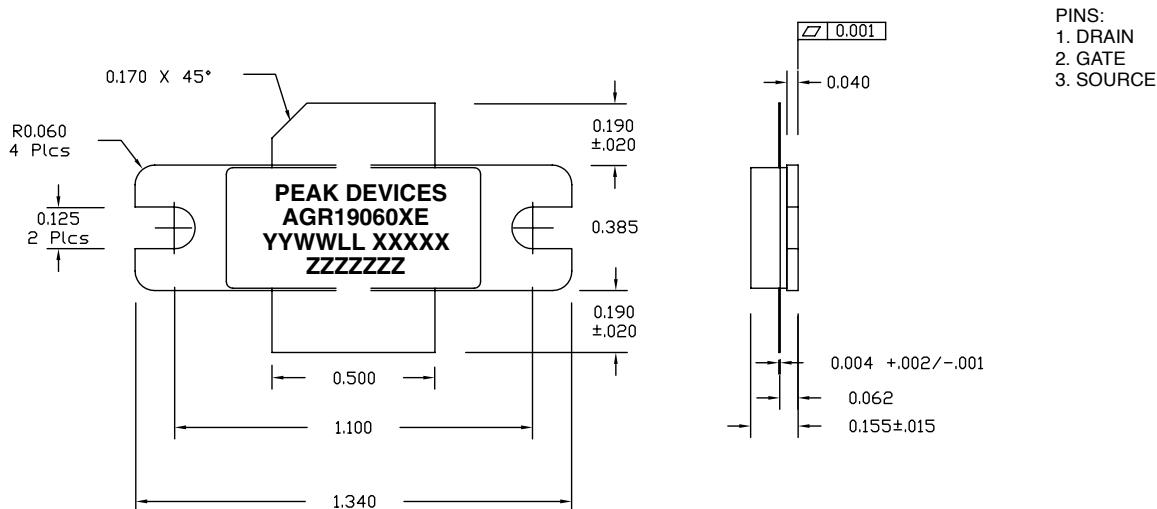
Package Dimensions

All dimensions are in inches. Tolerances are ± 0.005 in. unless specified.

AGR19060EU



AGR19060EF



Label Notes:

- M before the part number denotes model program. X before the part number denotes engineering prototype.
- The last two letters of the part number denote wafer technology and package type.
- YYWWLL is the date code including place of manufacture: year year work week (YYWW), LL = location (AL = Allentown, PA; BK = Bangkok, Thailand). XXXXX = five-digit wafer lot number.
- ZZZZZZ = seven-digit assembly lot number on production parts.
- ZZZZZZZZZZZZ = 12-digit (five-digit lot, two-digit wafer, and five-digit serial number) on models and engineering prototypes.